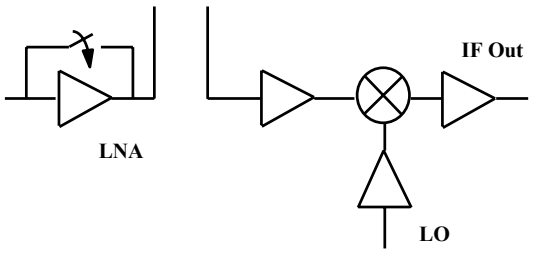
TriQuint SEMICONDUCTOR

GaAs MMIC CMH192

Datasheet

- High-Linearity, PCS LNA/Mixer IC for use in US and Korean band CDMA Mobile Phones
- Integrated bypass switch for LNA
- GaAs PHEMT Process
- Leadless 3.5 x 3.5 mm. SMT package
- LO Input power range: -7.0 to 0 dBm
- Operating voltage range: 2.7 to 4 V
- Total current consumption: 22 mA
- Adjustable Mixer Gain and IP3

ESD: **E**lectro**s**tatic **d**ischarge sensitive device
Observe handling Precautions!



Type	Marking	Ordering code (tape and reel)	Package
CMH192	**H192**	**Q62705-K608**	**VQFN-20**

Maximum Ratings	**Symbol**	**Value**		**Unit**
		min	**max**	
Supply Voltage	V_{DD}	0	6	V
DC-Voltage at RF Ports	V_{RF}	- 0.3	0.3	V
DC-Voltage at GND Ports	V_{GND}	- 0.3	0.3	V
DC-Voltage at CNTL Ports	V_{CNTL}	0	0.3 + V_{DD}	V
Power into LO Input	$P_{in,LO}$		10	dBm
Power into RF-IF Ports	Pin, RF		10	dBm
Operating Temperature	T_a	-40	85	°C
Channel Temperature	T_{Ch}		150	°C
Storage Temperature	T_{stg}	-55	150	°C

Thermal Resistance			
Channel to Soldering Point (GND)	R_{thChS}	102	°C /W

Electrical Characteristics 1

Parameter	min	typ	max	Unit
RF – Frequency / US	1930	-	1990	MHz
LO – Frequency / US (1)	1780	-	1940	MHz
RF – Frequency / Korean	1840	-	1870	MHz
LO – Frequency / Korean (1)	1590	-	1820	MHz
IF Frequency range	50	-	250	MHz
LO Power Input	-7.0	-	0.0	dBm
Supply Voltage (Vdd)	2.7	-	4.0	V
High Logic Level (H)	V_{DD} – 0.2	-	V_{DD}	V
Low Logic Level (L)	0.0	-	0.2	V

1) High-side LO is also supported

LNA – Performance of LNA

Test conditions: T_a = 25°C, V_{DD}= 2.7 V, PRF= -22 dBm, f_{RF} = 1960 MHz, LOW=GND, HIGH=Vdd

Mode – High Gain, High Linearity	min	typ	max	Unit
Operating Current		7		mA
Noise Figure		1.1		dB
Gain		12.5		dB
Input / Output return loss		10		dB
3rd Order Input Intercept Point		8.5		dBm
Mode – High Gain, Reduced Current	**min**	**Typ**	**max**	**Unit**
Operating Current		5		mA
Noise Figure		1.2		dB
Gain		12.3		dB
Input / Output return loss		10		dB
3rd Order Input Intercept Point		7.5		dBm
Mode – Low Gain, By-Pass Mode	**min**	**Typ**	**max**	**Unit**
Operating Current		0		mA
Noise Figure		4.5		dB
Gain		5		dB
Input / Output return loss		10		dB
3rd Order Input Intercept Point		25		dBm

MIXER - Electrical Characteristics of Mixer section

Test conditions: T_a = 25°C; V_{DD}= 2.7V, P_{LO} = -7 dBm,PRF=-22 dBm, f_{RF} = 1960 MHz, $f_{LO} = f_{RF} - f_{IF}$, f_{IF} = 210MHz, LOW=GND, HIGH=Vdd

Mode – High Linearity	**min**	**typ**	**max**	**Unit**
Operating Current		15		mA
Conversion Gain		15.0		dB
Noise Figure		3.5		dB
3rd Order Input Intercept Point		5.5		dBm
RF Input return loss		10		dB
LO Input return loss		10		dB
IF Output Impedance (1)		350 - j*515		Ω
Mode – Reduced Current	**min**	**typ**	**max**	**Unit**
Operating Current		12		mA
Conversion Gain		14.5		dB
Noise Figure		3.8		dB
3rd Order Input Intercept Point		4		dBm
RF Input return loss		10		dB
LO Input return loss		10		dB
IF Output Impedance (1)		350 - j*515		Ω

1) IF Output externally tuned to desired impedance

FULL CHAIN – LNA/Downconverter Characteristics

Test conditions: T_a = 25°C; V_{DD}= 2.7V, P_{LO} = -7 dBm, *PRF=-22 dBm,* f_{RF} = 1960 MHz, $f_{LO} = f_{RF} - f_{IF}$, f_{IF} = 210MHz, LOW=GND, HIGH=Vdd

Mode – High Gain, High Linearity	**min**	**typ**	**max**	**Unit**
Total operating Current		22.0		mA
Conversion Gain (1)		24.5		dB
Noise Figure		1.7		dB
Input IP3		-4.5		dBm
LNA Input IP3		10.0		dBm

1) Assumes 3 dB loss for image filter, value is calculated based on gain measurement of LNA and downconverter

FULL CHAIN – LNA/Downconverter Characteristics (continued)

Test conditions: T_a = 25°C; V_{DD}= 2.7V, P_{LO} = -7 dBm, *PRF=-22 dBm,* f_{RF} = 1960 MHz, $f_{LO} = f_{RF} - f_{IF}$, f_{IF} = 210MHz, LOS=GND, HIGH=Vdd

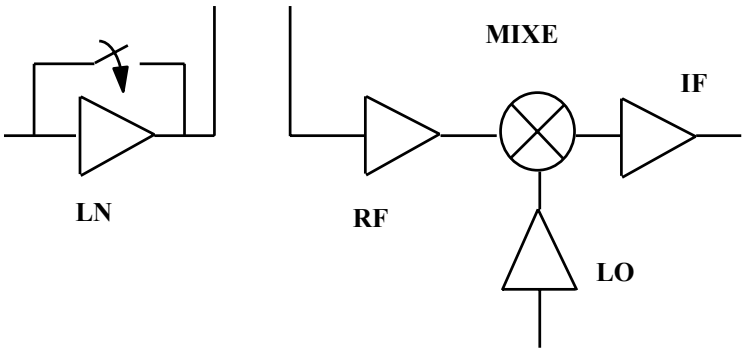
Mode – High Gain, Reduced Current	**min**	**typ**	**max**	**Unit**
Total operating Current		17		mA
Conversion Gain (1)		23.5		dB
Noise Figure		1.8		dB
Input IP3		-5.5		dBm
LNA Input IP3		7.5		dBm
Mode – Low Gain (LNA bypass)	**min**	**Typ**	**max**	**Unit**
Total operating Current		12		mA
Conversion Gain (1)		7.2		dB
Noise Figure		11.5		dB
Input IP3		11.5		dBm

1) Assumes 3.0 dB loss for image filter, value is calculated based on gain measurement of LNA and downconverter

Truth Table

	Control Voltage	
Operating Mode	**Gain Ctl**	**Rcv Only**
High Gain & Linearity	H	H
High Gain, Low Current	H	L
Low Gain	L	L

PIN Assignments & Functional Block Diagram

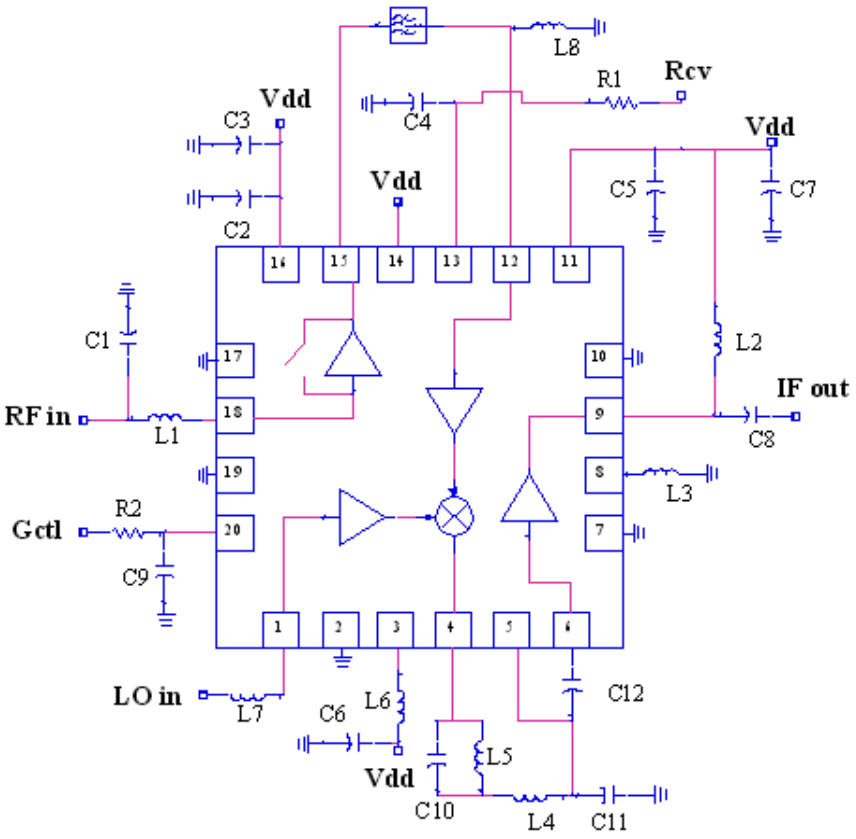


Pin Assignments:

PIN	Symbol	Description
1	LO in	LO Input
2	GND	Ground
3	LOA Vdd	Supply voltage for LO Buffer Amp
4	Mix Out	Mixer IF Output
5	IF Mtch	IF input match connection
6	IF In	IF amplifier input
7	GND	Ground
8	IFA src	IF Amplifier FET source ground
9	IFA out	IF Amplifier output
10	GND	Ground
11	RFA Vdd	Supply voltage for RFA
12	RFA in	Mixer input from image filter
13	Rcv	Current mode control
14	Vdd	Supply voltage
15	LNA out	RF output of LNA
16	LNA Vdd	Supply voltage for LNA
17	GND	Ground
18	LNA in	RF Input to LNA
19	GND	Ground
20	Gctl	Gain mode control for LNA

Truth Table:

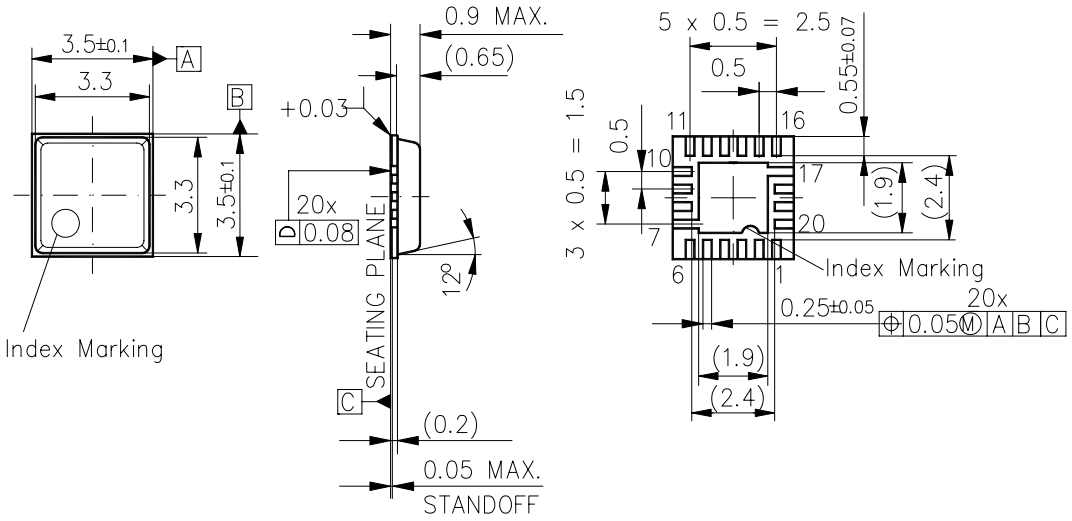
Applications Circuit:



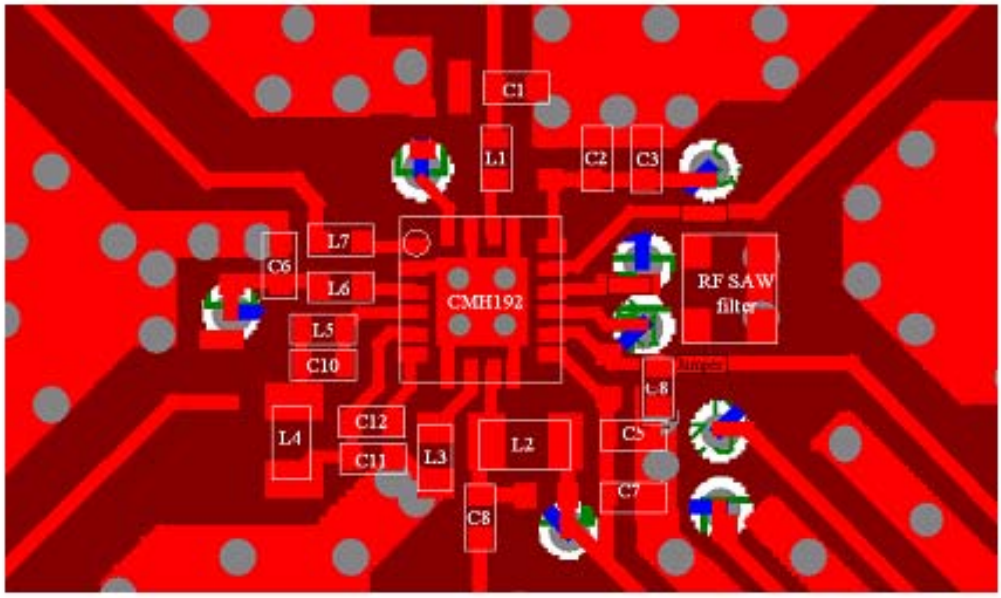
Component	Description	Package Type
C1	CAP, 1 pF	0402
C2	CAP, 22 pF	0402
C3	CAP, 10K pF	0402
C4	CAP, 100 pF	0402
C5	CAP, 22 pF	0402
C6	CAP, 1000 pF	0402
C7	CAP, 10K pF	0402
C8	CAP, 3.3 pF	0402
C9	CAP, 100 pF	0402
C10	CAP, 2 pF	0402
C11	CAP, 4 pF	0402

Component	Description	Package Type
C12	CAP, 100 pF	0402
L1	IND, 5.6 nH	0402
L2	IND, 120 nH	0603
L3	IND, 100 nH	0603
L4	IND, 82 nH	0603
L5	IND, 2.7 nH	0402
L6	IND, 5.6 nH	0402
L7	IND, 5.6 nH	0402
L8	IND, 12 nH	0402
R1	RES, 100 KOHM	0402
R2	RES,100 KOHM	0402

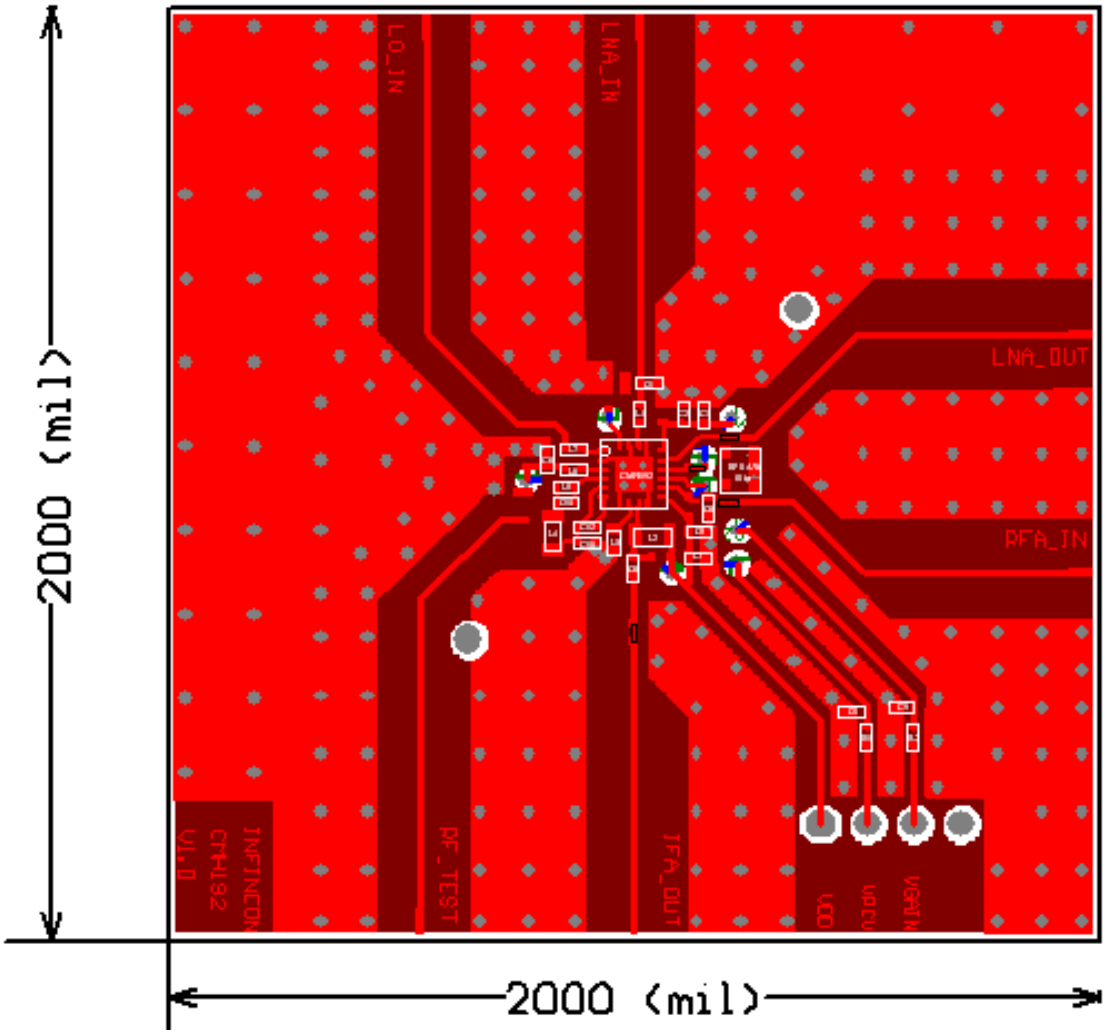
Package Outline – VQFN 20



Recommended PCB Layout:



Evaluation Board:



CMH192 – Application Information

DC Biasing:

Supply Voltage

One regulated voltage source is needed for CMH192. On the evaluation board it is labeled VDD.

Minimum LO Power for Proper Biasing

For proper biasing of the CMH192, a minimum LO input power is required. If the part is turned ON without any LO drive applied all currents will be extremely high. The minimum LO required is approximately –9 dBm. Operation with LO input powers below the minimum value causes the current to increase in all amplifier stages. For higher LO input power levels the current stays relatively constant over a wide range of LO powers. Proper matching of the LO amplifier is also important to achieve the lowest current consumption and to minimize the required LO input power.

Adjustable Current Level

The CMH192 can operate in two different current/linearity modes: High Linearity (with higher current) and Reduced Current (lower linearity). To operate with reduced current the voltage on pin 13 (RCV) should be set LOW. Some additional current reduction can be achieved by reducing the voltage at pin 14 by placing a resistor between VDD and pin 14. The current pulled by pin 14 is approximately 1 mA. Higher currents can be realized by using a higher VDD voltage.

Tuning LO and IF Amplifiers:

The CMH192 can be tuned to utilize either high or low side LO frequencies and allows a wide range of IF frequencies. Depending on the chosen frequency plan the off chip components for the LO and IF amplifiers will need to be optimized. An application circuit with all component values is provided for low side LO injection with IF frequency of 210 MHz (RF freq 1930 – 1960 MHz)

Two external components (L6 and L7) are required for tuning the LO. L6 is critical for setting the minimum current and to achieve the constant DC current over the operating band. L7 sets the LO input match.

Components L4, C9 and C11 form the input match for the IF amplifiers and will vary depending on the chosen IF frequency. The inductor on pin 8 allows adjustment to the gain of the IF amplifier.

Output matching components shown in the application circuit provide a transformation for a 50 Ohm load impedance. The output impedance for the IFA (looking into pin 9) at 210 MHz is approximately (350 - j*515) Ohms.

Downconverter Gain Adjustment:

The **Downconverter gain can be adjusted by changing the source feedback inductor L3 for the IFA**. Higher inductance will give lower downconverter gain and typically improve the IIP3.

Gain/Current Control Pins:

LOW = 0 to 0.2 V
HIGH = Vdd to (Vdd – 0.2) V

VGAIN – select between high and low gain states in the LNA.
VGAIN = HIGH: LNA ON (~12 dB Gain, ~ 6.5 mA current)
VGAIN = LOW: LNA bypassed (~ 4 dB Loss, no current)

VRCV - selects Current/Linearity mode (changes current in LNA/RFA/IFA)
VRCV = LOW selects Reduced Current Mode
VRCV = HIGH selects High Linearity Mode.

Other Notes:

Inductor L1 is critical for setting the Noise Figure of the LNA. A high Q wire wound inductor (e.g. Coilcraft) is recommended to achieve minimum NF.

Inductor L5 and Capacitor C10 form a “tank circuit” to terminate the RF in the mixer. These components should be placed in parallel close to pin 4. These elements may require tuning depending on component vendor and board parasitics to achieve flat conversion gain vs. frequency.

Inductor L8 is necessary for proper operation of the circuit for ESD protection.

Lower RF frequencies (i.e. Korean PCS or GPS) may be accommodated by adding inductance between the LNA and RFA VDD pins and their bypass capacitors.

LNA current can be determined by subtracting the current in Low Gain mode from the current in High Gain mode (keeping VRCV and VMODE constant).

Control lines (G_CNTL, VRCV and VMODE) have an input impedance of greater than 1 MΩ when Vdd is ON. When VDD is off, they have approximately 20 KΩ input impedance.

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